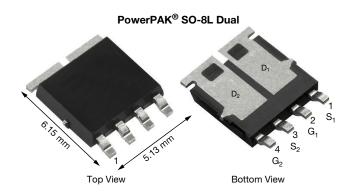
Vishay Siliconix

# Automotive Dual N-Channel 30 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V <sub>DS</sub> (V)	30
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.007
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 4.5 \text{ V}$	0.0086
I <sub>D</sub> (A) per leg	30
Configuration	Dual

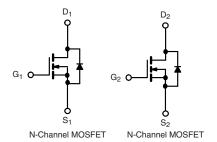
#### **FEATURES**

- TrenchFET® Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested
- AEC-Q101 Qualified<sup>d</sup>
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SQJ910AEP (for detailed order number please see <a href="https://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

ABSOLUTE MAXIMUM RATING	<b>S</b> (T <sub>C</sub> = 25 °C, unles	ss otherwise noted	)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	30	V
Gate-Source Voltage		$V_{GS}$	± 20	V
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 25 °C	1	30	
Continuous Diain Current	T <sub>C</sub> = 125 °C	l <sub>D</sub>	30	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	30	Α
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	120	
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	29	
Single Pulse Avalanche Energy	L = U.1 IIIII	E <sub>AS</sub>	42	mJ
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	48	W
Maximum Fower Dissipation	$T_C = 125 ^{\circ}\text{C}$	16	VV	
Operating Junction and Storage Temperatur	e Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature) <sup>e, f</sup>			260	

THERMAL RESISIANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	85	°C/W
Junction-to-Case (Drain)		$R_{thJC}$	3.1	G/ VV

#### **Notes**

- a. Package limited
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. Parametric verification ongoing
- e. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static				l			ı
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> :	= 0 V, I <sub>D</sub> = 250 μA	30	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$		1.5	2	2.5	l v
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 30 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 30 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 30 V, T <sub>J</sub> = 175 °C	-	-	150	1
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
Drain-Source On-State Resistance <sup>a</sup> Forward Transconductance <sup>b</sup> <b>Dynamic</b> <sup>b</sup>		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 12 A	-	0.0058	0.007	
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 10.7 A	-	0.0072	0.0086	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 12 A, T <sub>J</sub> = 125 °C	-	-	0.0096	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 12 A, T <sub>J</sub> = 175 °C	-	-	0.012	•
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	$V_{DS}$	= 15 V, I <sub>D</sub> = 12 A	-	72	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	1495	1869	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 15 \text{ V}, f = 1 \text{ MHz}$	-	313	391	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	126	158	
Total Gate Charge <sup>c</sup>	Qg			-	25.8	39	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 15 \text{ V}, I_{D} = 11.3 \text{ A}$	-	4.3	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1		-	4.3	-	
Gate Resistance	R <sub>g</sub>		f = 1 MHz	0.6	1.38	2.10	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	11	16	
Rise Time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	= 15 V, R <sub>L</sub> = 1.4 Ω	-	3	4	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 1 A$ ,	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	27	40	ns
Fall Time <sup>c</sup>	t <sub>f</sub>	- 7		7	11		
Source-Drain Diode Ratings and Char-	acteristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	120	Α
Forward Voltage	V <sub>SD</sub>	I <sub>E</sub> = 7.8 A, V <sub>GS</sub> = 0 V			0.77	1.2	V

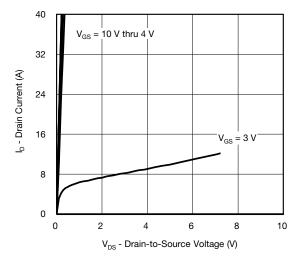
### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

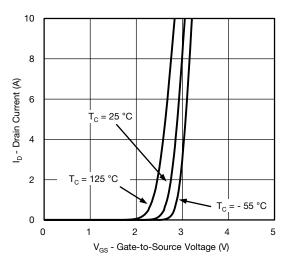
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



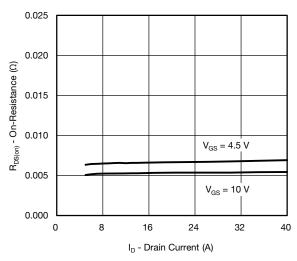
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



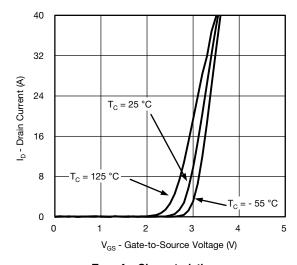
#### **Output Characteristics**



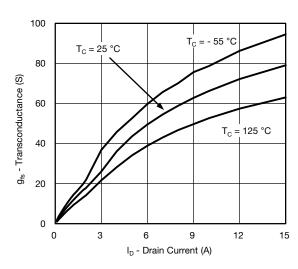
## Transfer Characteristics



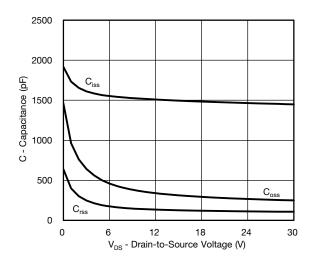
On-Resistance vs. Drain Current



#### **Transfer Characteristics**



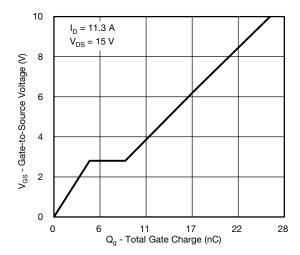
#### Transconductance



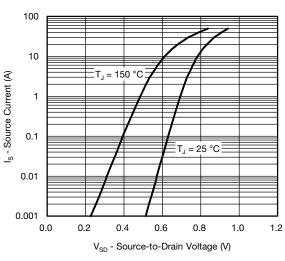
Capacitance



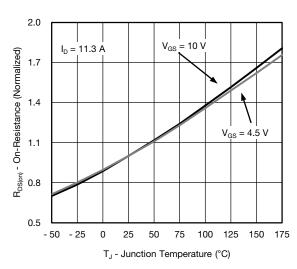
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



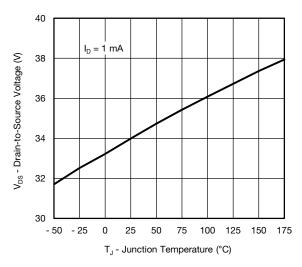
#### **Gate Charge**



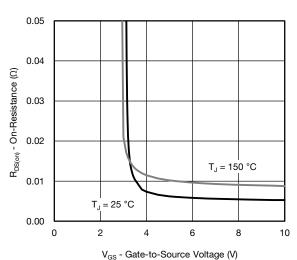
## Source Drain Diode Forward Voltage



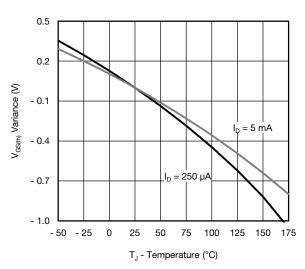
On-Resistance vs. Junction Temperature



#### Drain-Source Breakdown vs. Junction Temperature



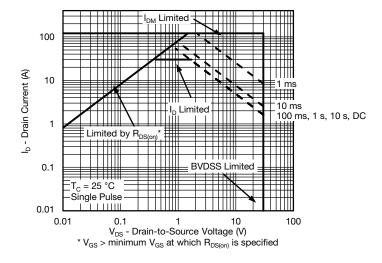
On-Resistance vs. Gate-to-Source Voltage



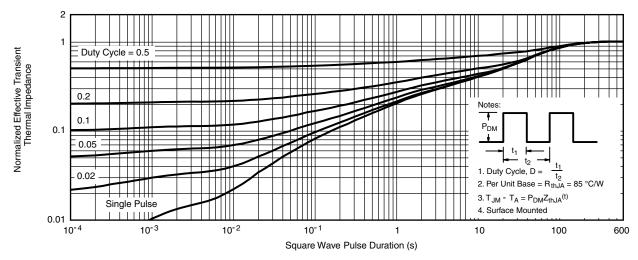
Threshold Voltage



## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



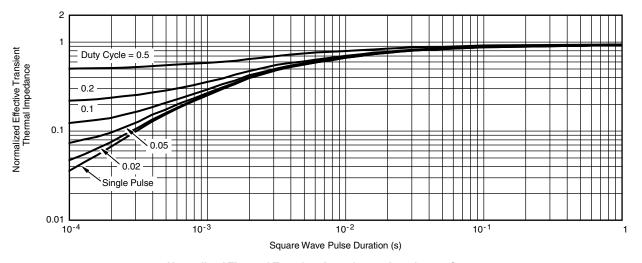
### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg263748">www.vishay.com/ppg263748</a>.



# PowerPAK® SO-8L Case Outline 2



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DIM	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN. NOM.		MAX.	
Α	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
Е	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
E3	6.05	6.22	6.40	0.238	0.245	0.252	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51			0.020		
W	0.23		0.009				
W1		0.41		0.016			
W2	2.82		0.111				
W3		2.96		0.117			
θ	0°	-	10°	0°	-	10°	

DWG: 6044

#### Note

• Millimeters will govern



### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)



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